

NPN SMALL SIGNAL TRANSISTOR IN SOT323

Description

AC847BWQ and AC847CWQ Bipolar Junction Transistors (BJT) are designed to meet the stringent requirements of Automotive Applications.

Features

- Ideally Suited for Automatic Insertion
- Complementary PNP Types: AC857BWQ AC857CWQ
- · For Switching and AF Amplifier Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

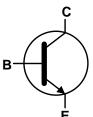
Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202. Method 208 [®]3
- Weight: 0.006 grams (Approximate)

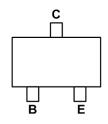




Top View



Device Symbol



Top View Pin-Out

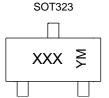
Ordering Information (Notes 4 & 5)

Part Number	Compliance	Marking	Reel Size (inches)	Quantity Per Reel
AC847BWQ-7	Automotive	2D6	7	3,000
AC847BWQ-13	Automotive	2D6	13	10,000
AC847CWQ-7	Automotive	2D3	7	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



XXX = Product Type Marking Code
(Please see Ordering Information)
YM = Date Code Marking
Y or Y = Year (ex: E = 2017)
M or M = Month (ex: 9 = September)

Date Code Key

Year	2017		2018	2019		2020	2021		2022	2023		2024
Code	Е		F	G		Н			J	K		L
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	6	V
Continuous Collector Current	Ic	100	mA
Peak Collector Current	I _{CM}	200	mA
Peak Base Current	I _{BM}	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)	P _D	200	mW
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C	

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

^{6.} For a device mounted on minimum recommended pad layout 1oz weight copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

^{7.} Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic				Min	Тур	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage				50	_		>	$I_C = 100\mu A$	
Collector-Emitter Breakdown Voltage (Note 8)			BV _{CEO}	45	_		>	I _C = 10mA	
Emitter-Base Breakdown Volta	Emitter-Base Breakdown Voltage			6	_		>	$I_E = 100\mu A$	
DC Current Gain (Note 8)	Current Gain Group	В	h _{FE}	200	290	450		$V_{CF} = 5.0V, I_{C} = 2.0mA$	
Do Current Gain (Note o)	Current Gain Group	С	IIFE	420	520	800	_	VCE = 5.0V, IC = 2.0IIIA	
Collector Cutoff Current			lana			20	nA	V _{CB} = 30V	
Collector Cutoff Current			I _{CBO}			5	μΑ	V _{CB} = 30V, T _A = +150°C	
Collector-Emitter Saturation V	oltago (Noto 9)				90	250	mV	$I_C = 10mA, I_B = 0.5mA$	
Collector-Emitter Saturation v	ollage (Note 6)		V _{CE(SAT)} —	200	600	IIIV	$I_C = 100 \text{mA}, I_B = 5.0 \text{mA}$		
D			.,	580	660	700	mV	$I_C = 2mA$, $V_{CE} = 5V$	
Base-Emitter Turn-On Voltage	(Note o)		V _{BE(ON)}	_	_	770	mv	I _C = 10mA, V _{CE} = 5V	
Page Facilities Octobration Malage (Nation)			.,		700		>/	$I_C = 10mA, I_B = 0.5mA$	
Base-Emitter Saturation Voltage	ge (Note 8)		V _{BE(SAT)}	_	900	_	mV	$I_C = 100 \text{mA}, I_B = 5 \text{mA}$	
Output Capacitance			C _{OBO}	_	3	4.5	pF	V _{CB} = 10V, f = 1.0MHz	
Transition Frequency			f⊤	100	300	_	MHz	$V_{CE} = 5V, I_{C} = 10mA,$ f = 100MHz	
Noise Figure		NF	_	_	10	dB	V_{CE} = 5V, I_{C} = 200 μ A R_{S} = 2k Ω , f = 1kHz Δf = 200Hz		

Note:

8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

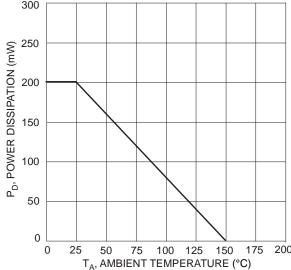
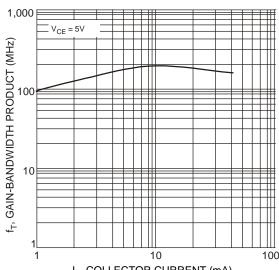


Figure 1 Power Dissipation vs. Ambient Temperature



I_C, COLLECTOR CURRENT (mA) Figure 3 Typical Gain-Bandwidth Product vs. Collector Current

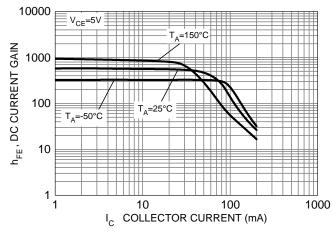


Figure 5 Typical DC Current Gain vs. Collector Current (Band C Group Gain)

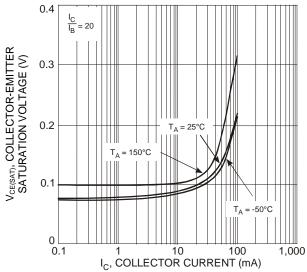


Figure 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

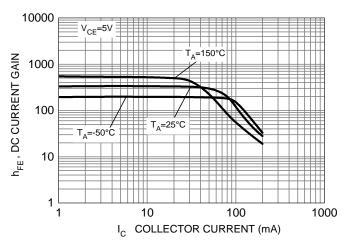


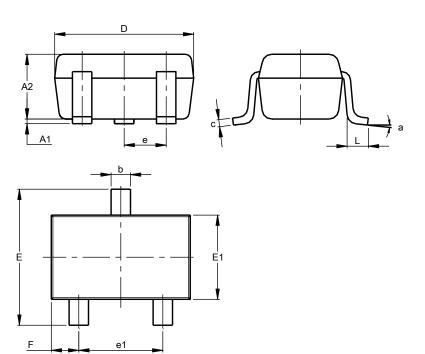
Figure 4 Typical DC Current Gain vs. Collector Current (Band B Group Gain)



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323

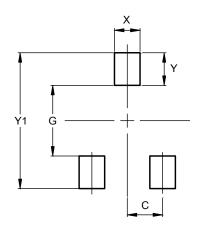


SOT323						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	0.95			
b	0.25	0.40	0.30			
С	0.10	0.18	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	().650 B	SC			
e1	1.20	1.40	1.30			
F	0.375	0.475	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500



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